



D

S2

N-Channel

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low Gate Charge
- Low R_{DS(ON)}:
 - 24mΩ @V_{GS} = 4.5V
 - $28m\Omega$ @V_{GS} = 2.5V
 - 34mΩ @V_{GS} = 1.8V
 - Low Input/Output Leakage
- ESD Protected up to 2kV HBM
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

Mechanical Data

Case: SOT-26

G,

 D_1/D_2

 G_2

- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208

D

S1

Equivalent Circuit

N-Channel

- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.0008 grams (approximate)





SOT-26

S₁

D₁/D₂

 S_2

Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit		
Drain-Source Voltage		V _{DSS}	20	V		
Gate-Source Voltage		V _{GSS}	±12	V		
Drain Current (Note 1) Continuous	T _A = 25°C T _A = 70°C	ID	6.5 5.2	А		
Pulsed Drain Current (Note 2)		I _{DM}	30	А		

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	0.85	W
Thermal Resistance, Junction to Ambient (Note 1) t ≤10s	R _{0JA}	147	°C /W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	O°

Notes: 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s.

2. Repetitive Rating, pulse width limited by junction temperature.

3. No purposefully added lead.

4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

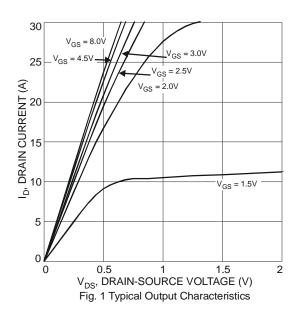


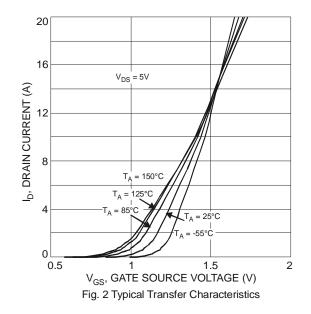
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
STATIC CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Body Leakage Current	Igss	_	_	±10	μΑ	$V_{DS} = 0V, V_{GS} = \pm 10V$
Gate-Source Breakdown Voltage	BV _{SGS}	±12	-	-	V	$V_{DS} = 0V, I_G = \pm 250 \mu A$
Gate Threshold Voltage	V _{GS(th)}	0.5	_	0.9	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}	_	17 20 26	24 28 34	mΩ	$V_{GS} = 4.5V, I_D = 6.5A$ $V_{GS} = 2.5V, I_D = 5.5A$ $V_{GS} = 1.8V, I_D = 3.5A$
Forward Transfer Admittance	Y _{FS}	_	8	—	S	$V_{DS} = 10V, I_D = 5A$
Diode Forward Voltage (Note 5)	V _{SD}	_	0.7	1.0	V	I _S = 2.25A, V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 6)				-		-
Input Capacitance	Ciss		143	—	pF	
Output Capacitance	C _{oss}	—	74	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	29	—	pF	1 - 1.00012
Gate Resisitance	R _G	_	202	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$
SWITCHING CHARACTERISTICS						
Total Gate Charge	Qg	_	8.8	—	nC	
Gate-Source Charge	Q _{gs}	_	1.4	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Drain Charge	Q _{gd}	_	3.0	_	nC	
Turn-On Delay Time	t _{D(on)}	_	53	_	ns	
Turn-On Rise Time	tr		78	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	562	_	ns	$R_L = 10\Omega, R_G = 6\Omega$
Turn-Off Fall Time	tf	_	234	_	ns	

Notes: 5. Test pulse width t = 300ms.

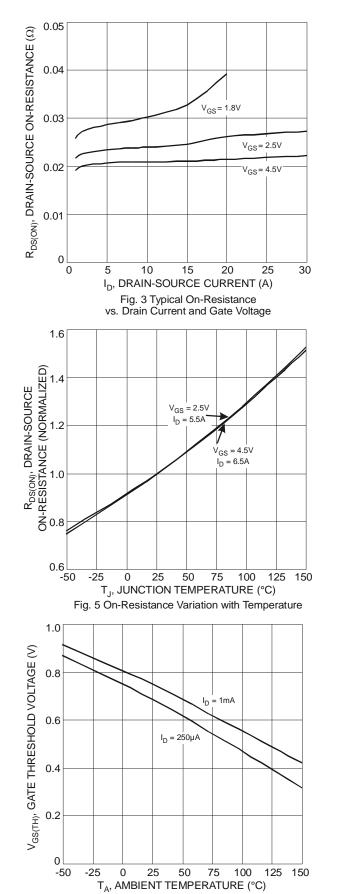
6. Guaranteed by design. Not subject to production testing.

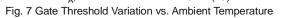


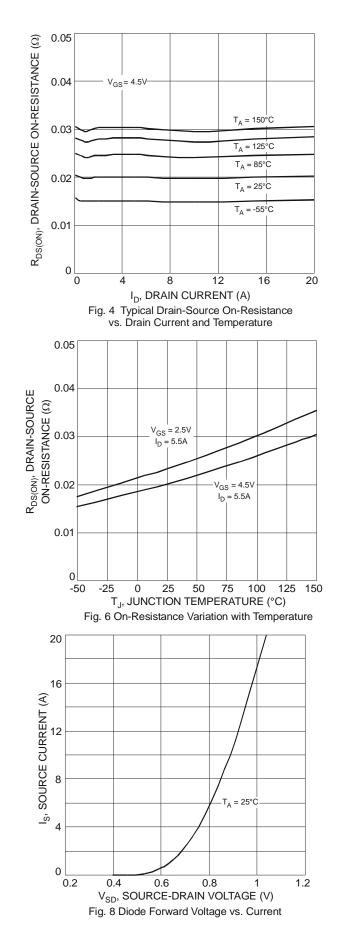




NEW PRODUCT

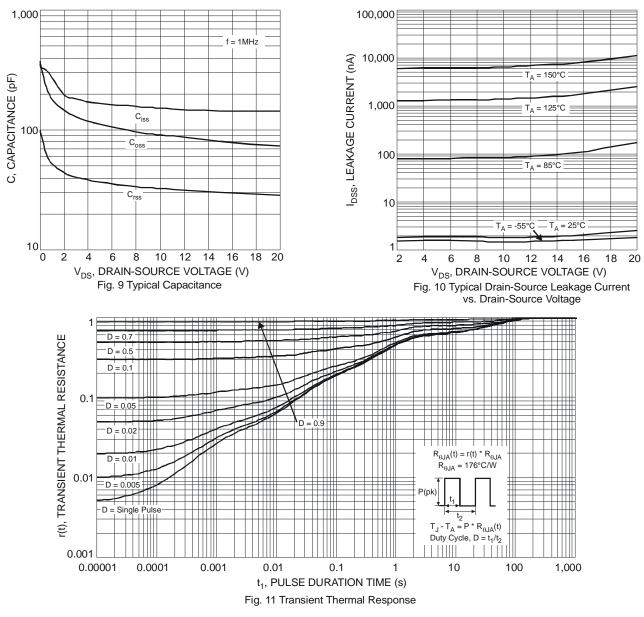








DMG6968UDM

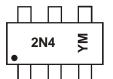


Ordering Information (Note 7)

Part Number	Case	Packaging
DMG6968UDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



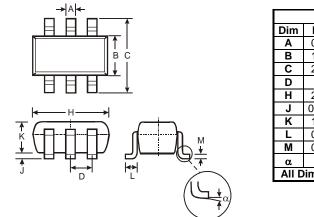
2N4 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key	
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Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

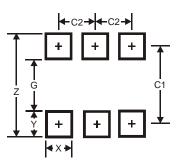


Package Outline Dimensions



SOT-26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D			0.95			
Η	2.90	3.10	3.00			
J	0.013	0.10	0.05			
Κ	1.00	1.30	1.10			
L	0.35	0.55	0.40			
Μ	0.10	0.20	0.15			
α	0°	8°	_			
All D	imensi	ons in	mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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